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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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Medium Power AF Schottky Diode

• Forward current: 1 A

• Reverse voltage: 30 V

Very low forward voltage

(typ. 0.41V @ $I_F = 1A$)

 For high efficiency DC/DC conversion, fast switching, protection and clamping applications

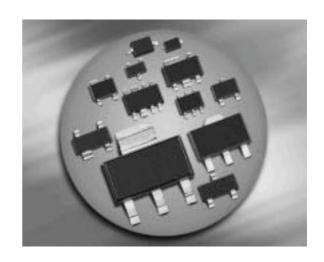
- Pb-free (RoHS compliant) package 1)
- Qualified according AEC Q101





BAS 3010A-03W





Туре	Package	Configuration	Marking
BAS3010A-03W	SOD323	single	4/ blue

Maximum Ratings at $T_A = 25$ °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage ²⁾	V_{R}	30	V
Forward current ²⁾	I _F	1	Α
Average rectified forward current (50/60Hz, sinus)	I _{FAV}	1	
Repetitive peak forward current	/ _{FRM}	3.5	
$(t_{\rm p} \le 1 {\rm ms}, \ D \le 0.5)$			
Non-repetitive peak surge forward current	I _{FSM}	10	
(<i>t</i> ≤ 10ms)			
Junction temperature	Ti	150	°C
Operating temperature range	Top	-65 125	
Storage temperature	T _{stq}	-65 150	

¹Pb-containing package may be available upon special request

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 $^{^2}$ For T_A > 25°C the derating of V_R and I_F has to be considered. Please refer to the attached curves.



Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}	≤ 82	K/W

Electrical Characteristics at T_{Λ} = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current ²⁾	I _R				μΑ
V _R = 5 V		-	5	25	
V _R = 10 V		-	10	50	
V _R = 30 V		-	40	200	
Forward voltage ²⁾	V _F				mV
I _F = 1 mA		-	170	220	
<i>I</i> _F = 10 mA		-	220	270	
$I_{\rm F}$ = 100 mA		_	290	340	
I _F = 500 mA		_	350	410	
<i>I</i> _F = 1 A			410	470	
AC Characteristics		·	-	· · · · · · · · · · · · · · · · · · ·	
Diode capacitance	C _T	-	28	35	pF
$V_{R} = 5 \text{ V}, f = 1 \text{ MHz}$					

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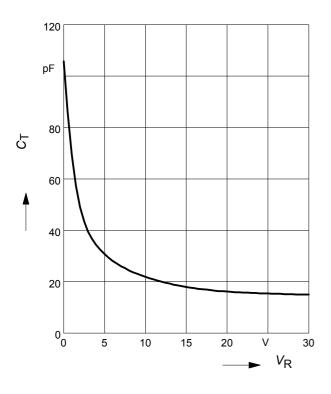
 $^{^{\}rm 1}{\rm For}$ calculation of $R_{\rm thJA}$ please refer to Application Note Thermal Resistance

²Pulsed test: $t_{\rm p}$ = 300 µs; D = 0.01



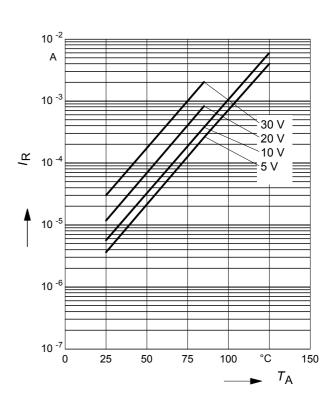
Diode capacitance $C_T = f(V_R)$

f = 1MHz



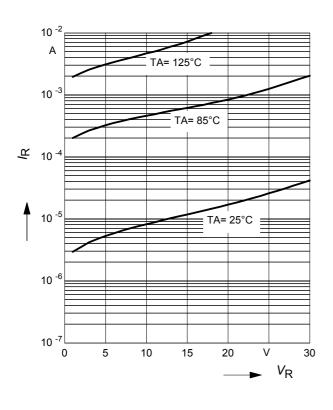
Reverse current $I_R = f(T_A)$

 V_{R} = Parameter



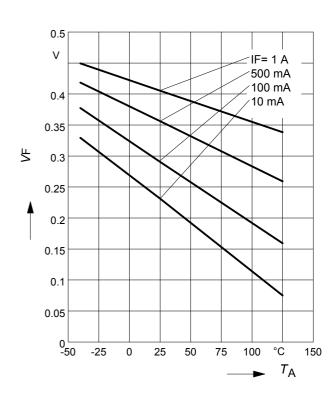
Reverse current $I_R = f(V_R)$

 T_A = Parameter



Forward Voltage $V_F = f(T_A)$

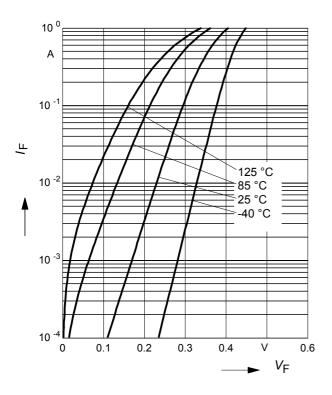
 I_{F} = Parameter





Forward current $I_F = f(V_F)$

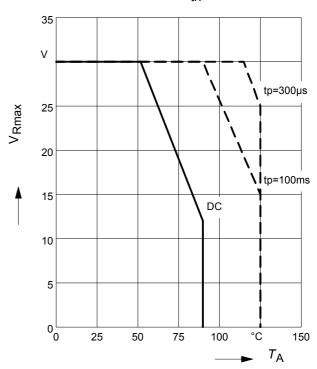
 T_A = Parameter



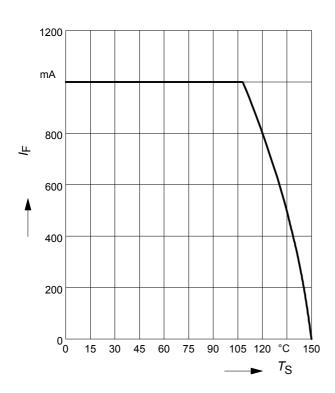
Permissible Reverse voltage $V_R = f(T_A)$

 t_p = Parameter, Duty cycle < 0.01

Device mounted on PCB with R_{th} = 160 k/W



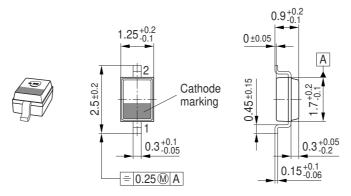
Forward current $I_F = f(T_S)$



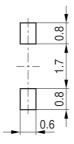
4



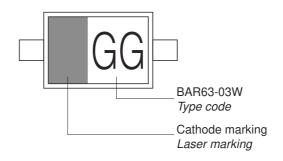
Package Outline



Foot Print

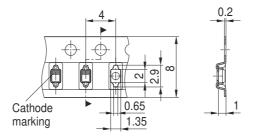


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel





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